

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1. (Currently amended) A semiconductor device structure, comprising:
a first layer comprising anti-reflective material; and
a second layer comprising silicon nitride, located over the first layer, and including ~~an arithmetic mean of~~ less than 1.23 in-film particles or surface roughness features per square millimeter of surface area.
2. (Previously presented) The semiconductor device structure of claim 1, wherein the anti-reflective material comprises silicon atoms and nitrogen atoms.
3. (Previously presented) The semiconductor device structure of claim 2, wherein the anti-reflective material further comprises oxygen atoms.
4. (Previously presented) The semiconductor device structure of claim 1, wherein the anti-reflective material comprises $\text{Si}_x\text{O}_y\text{N}_z$, where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.
5. (Previously presented) The semiconductor device structure of claim 1, wherein a surface of the first layer is substantially free of at least one of measurable particulates and surface roughness.
6. (Previously presented) The semiconductor device structure of claim 1, wherein the second layer includes, on average, less than $1\frac{1}{4}$ of at least one of particles and surface roughness features of at least about 120 nm dimension per square millimeter of surface area.

7. (Previously presented) The semiconductor device structure of claim 1, wherein the second layer is formed on the first layer.

8. (Currently amended) A semiconductor device structure, comprising:
a first layer comprising anti-reflective material; and
a second layer comprising silicon nitride, located over the first layer, and including an arithmetic mean of less than 1.23 in-film particles or surface roughness features of at least 120 nanometers size per square millimeter of surface area.

9. (Previously presented) The semiconductor device structure of claim 8, wherein the anti-reflective material comprises silicon atoms and nitrogen atoms.

10. (Previously presented) The semiconductor device structure of claim 9, wherein the anti-reflective material further comprises oxygen atoms.

11. (Previously presented) The semiconductor device structure of claim 8, wherein the anti-reflective material comprises $\text{Si}_x\text{O}_y\text{N}_z$, where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.

12. (Previously presented) The semiconductor device structure of claim 8, wherein a surface of the first layer is substantially free of at least one of measurable particulates and surface roughness.

13. (Canceled)

14. (Previously presented) The semiconductor device structure of claim 8, wherein the second layer is formed on the first layer.